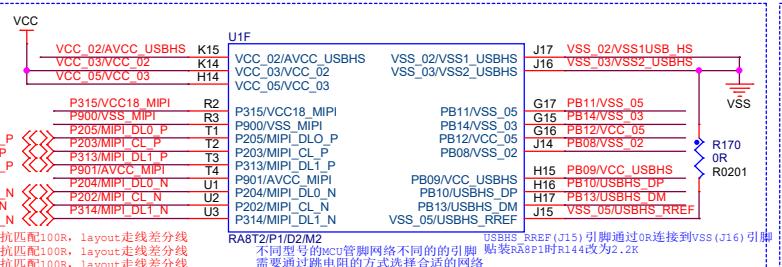


核心板芯片	R7KA8T2L	R7KA8P1K
C168-169	0.1uF	NC
C170	0.1uF	2.2uF
C171-C174	NC	0.1uF
C191-C192	NC	0.1UF
R145-R150	NC	NC
R151-R168	0R	NC
R170	0R	2.20K 1%
L171	NC	120R8100M
R172-R180	NC	0R
R191-R193	NC	0R

→ Page1: MCU 电源
Page2: MCU I/O
Page3: Jlink OB
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Page8: BTB



电阻选装

RABPI1/D2/M2和RAB8T2的部分膜内结构不同，通过选表阻差的方式，应对不同型号的IC贴表。默认贴表RAB8T2。

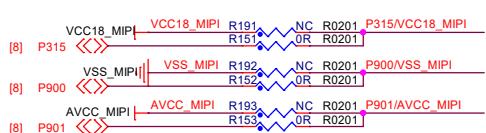
要贴的器件靠近MCU摆放，NC器件在MCU-BTB间任意摆放



与电源相关的引脚：MCU信号出来后立即用电阻分离

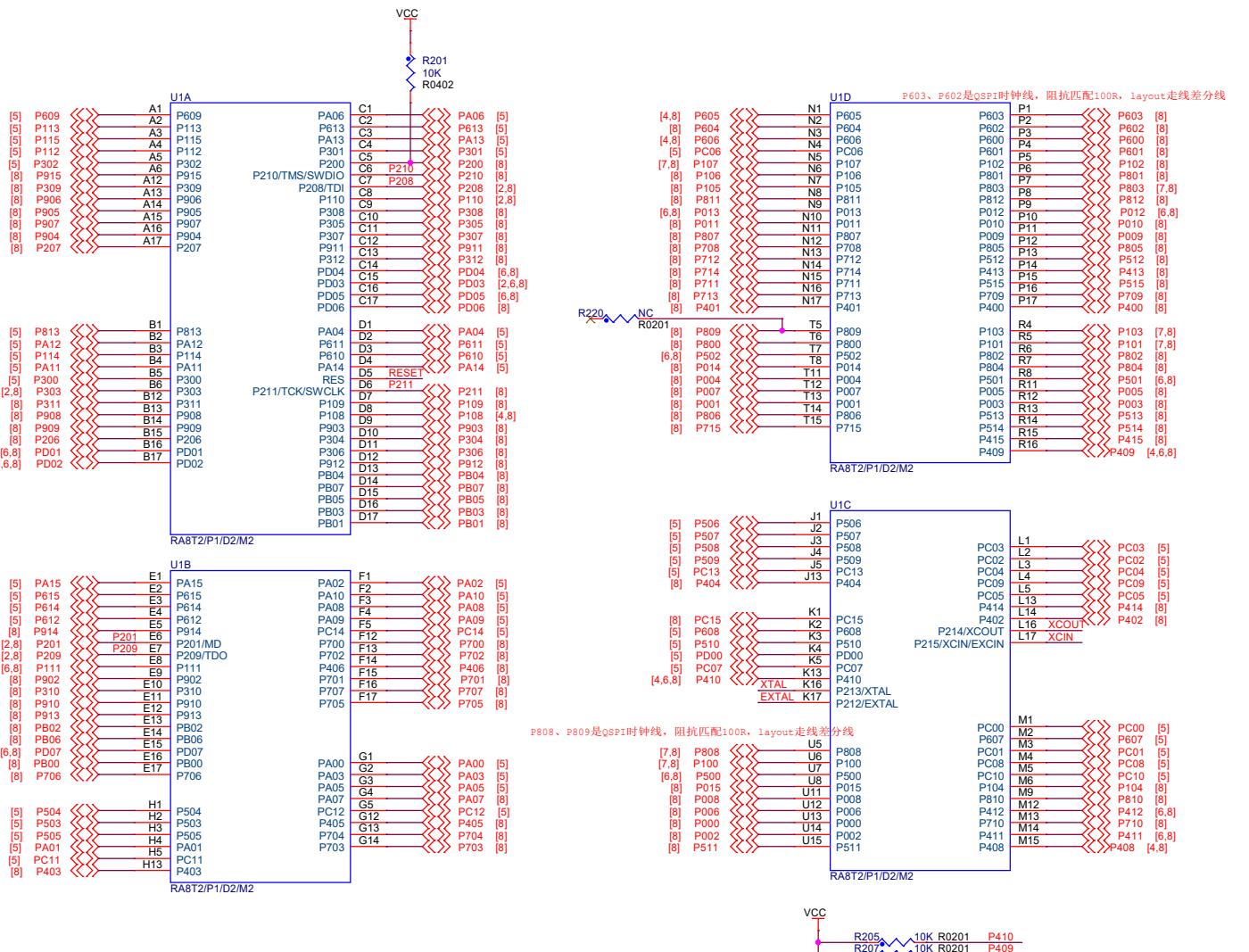
MIPI部分

要贴的器件靠近MCU摆放，NC器件在MCU-BTB间任意摆放

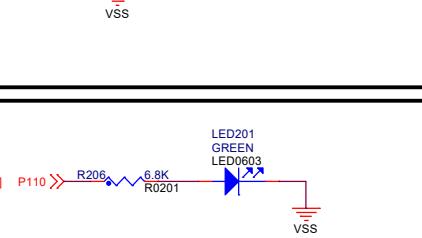
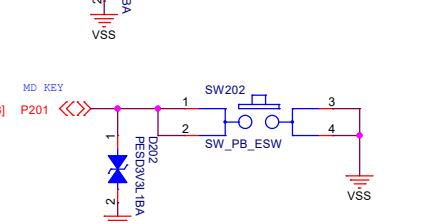
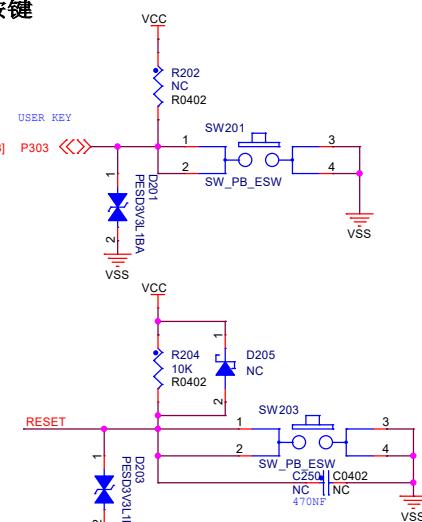


通孔拓展



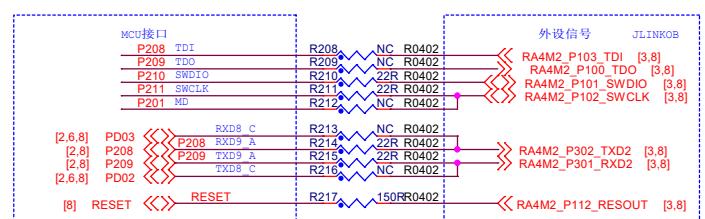


用户按键

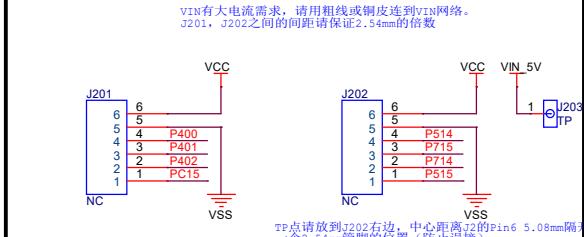


如果使用USB HS，主晶振只能选12/20/24/48MHz

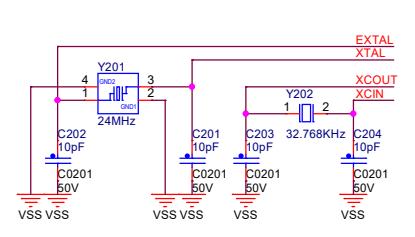
接口信号



通孔拓展



昌振

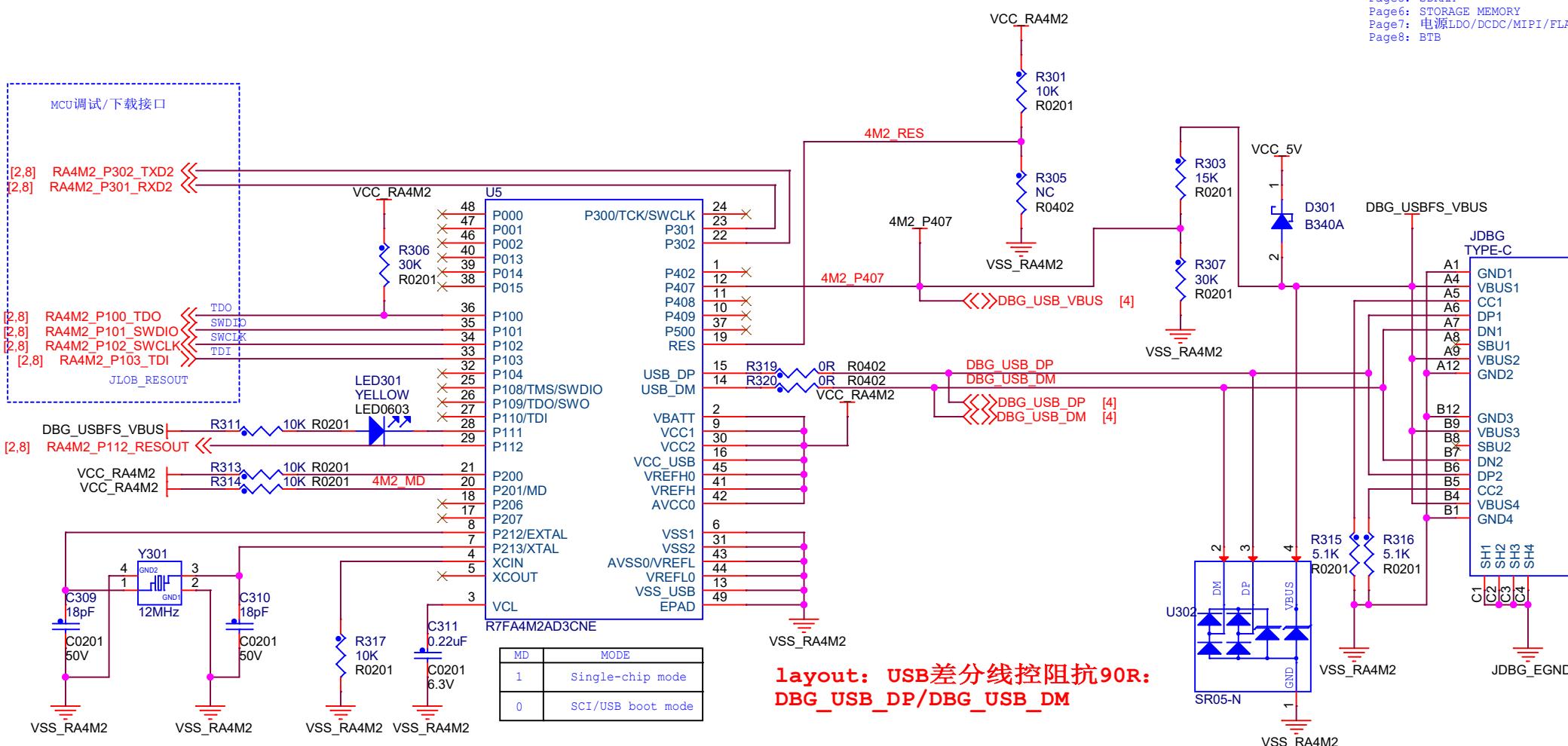


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Title 野火瑞萨CPKNET-RA8T2L 核心板		
Size A3	Document Number MCU IO	Rev. V1.1
Date: Wednesday, September 17, 2025		Sheet 2 of 10

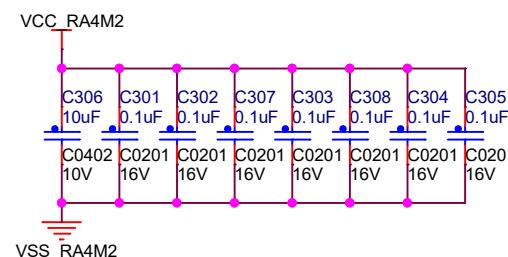
Jlink OB

注意: R7FA4M2只能12MHz晶振

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测试点 1.25间距/预留

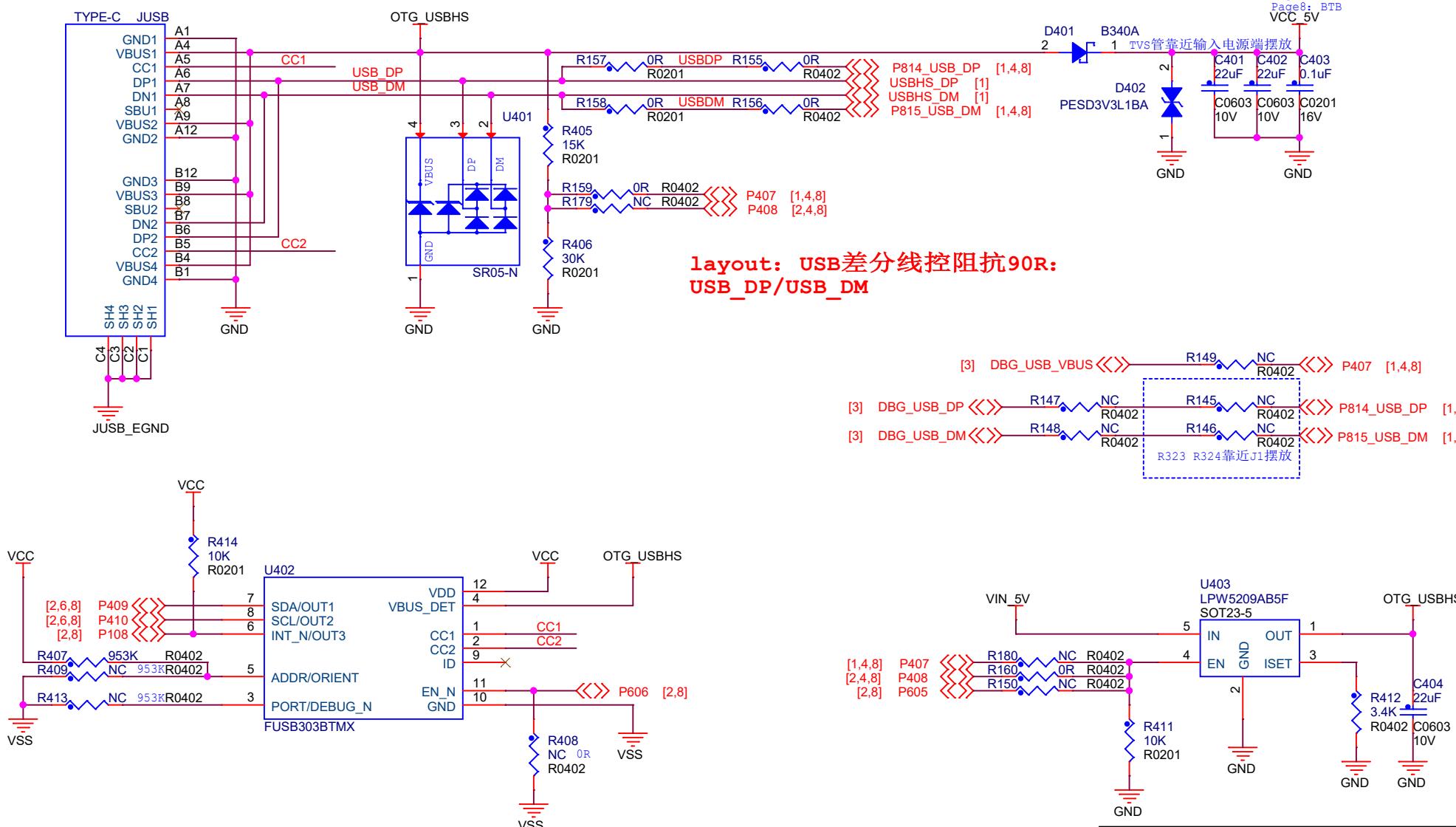


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Size A4	Document Number Jlink OB
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USB HS

如果使用USB HS, 主晶振只能选12/20/24/48MHz

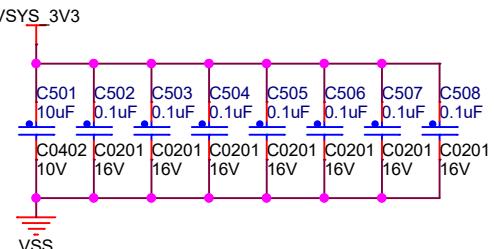
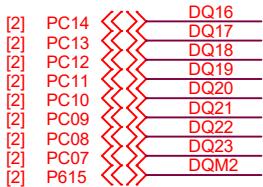
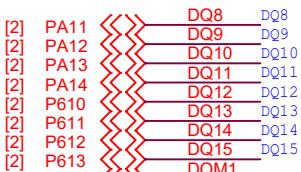
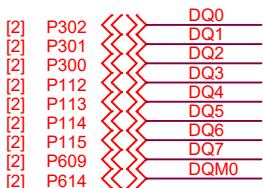
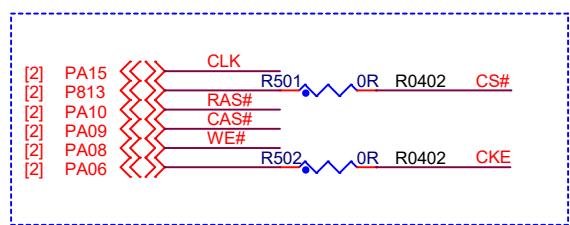
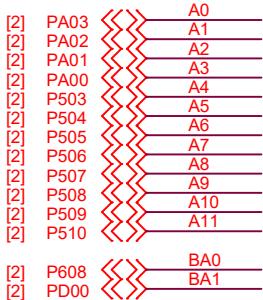
Page1: MCU 电源
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 VCC 5V



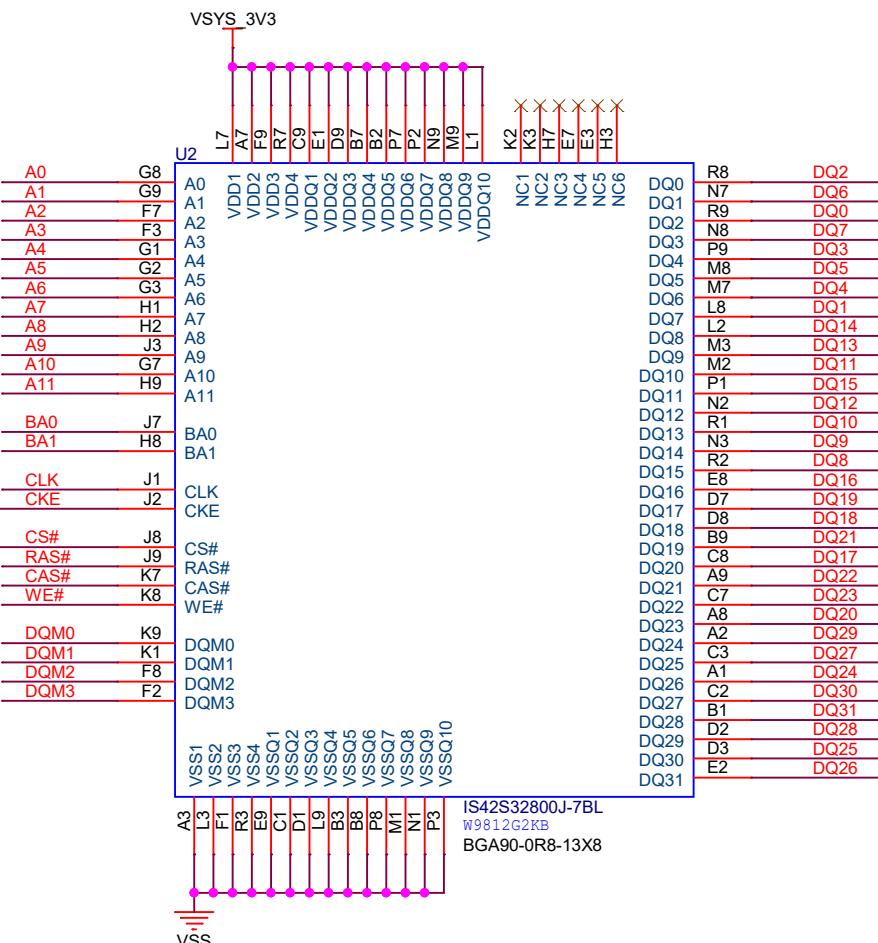
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SDRAM



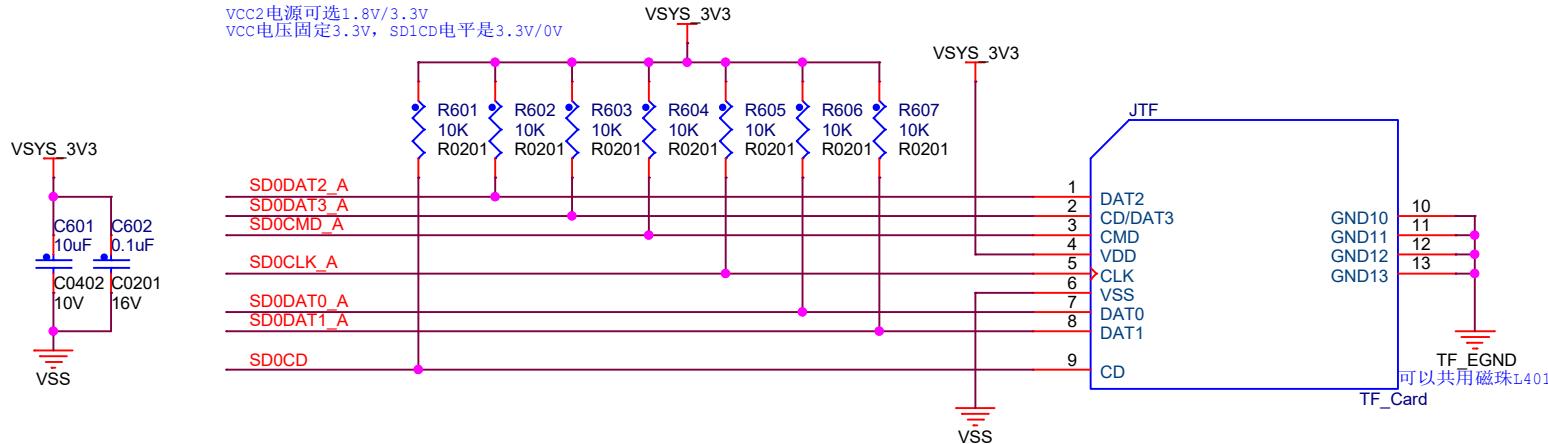
layout: SDRAM走线控阻抗50R:



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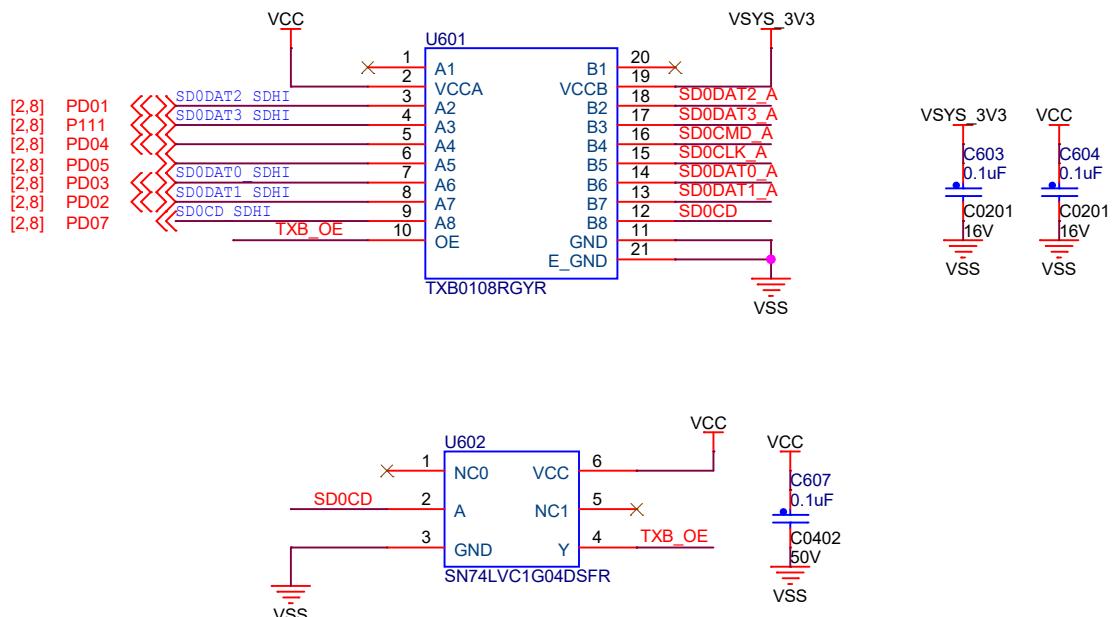
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SD卡

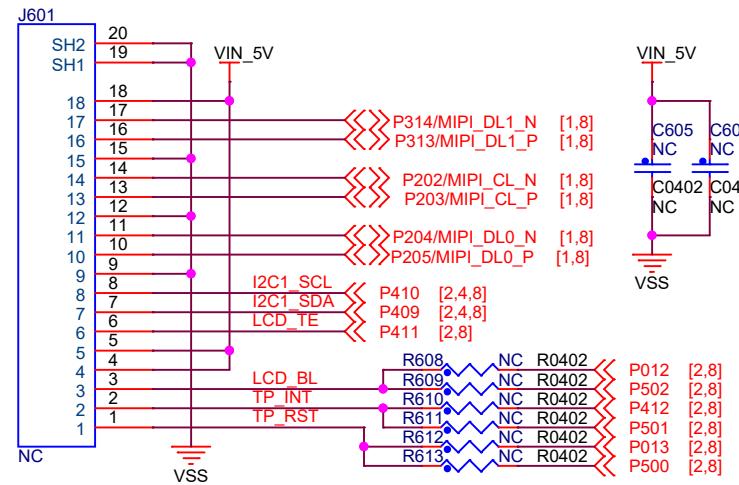


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SD卡电平转换

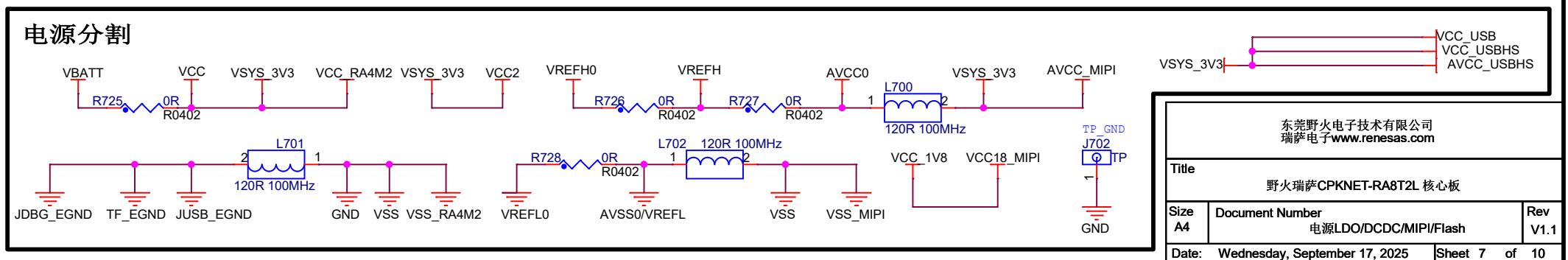
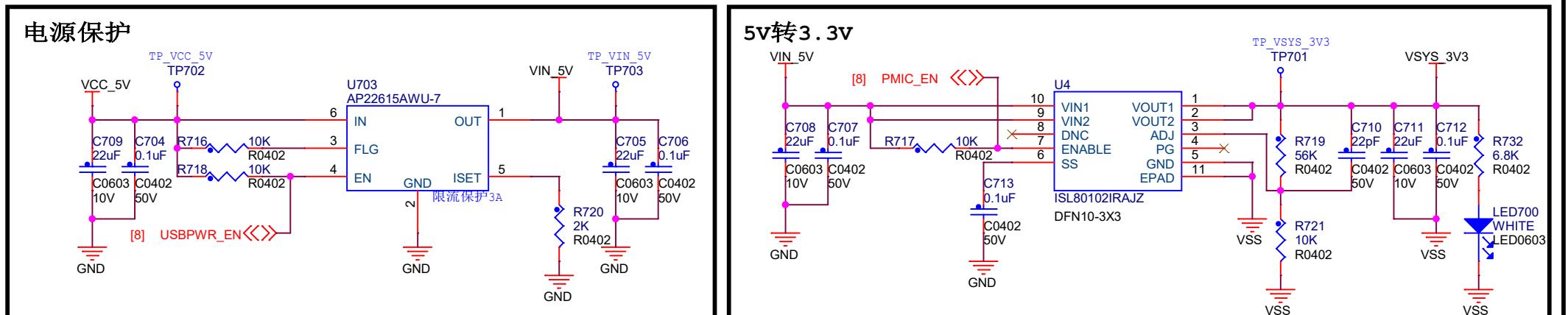
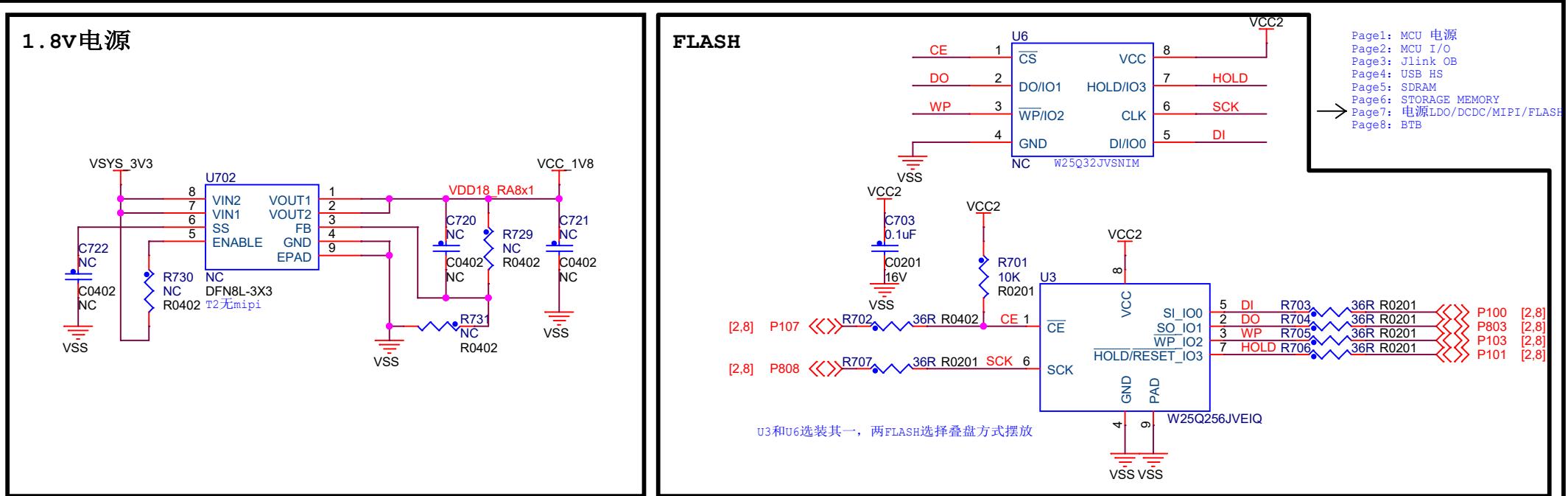


MIPI屏



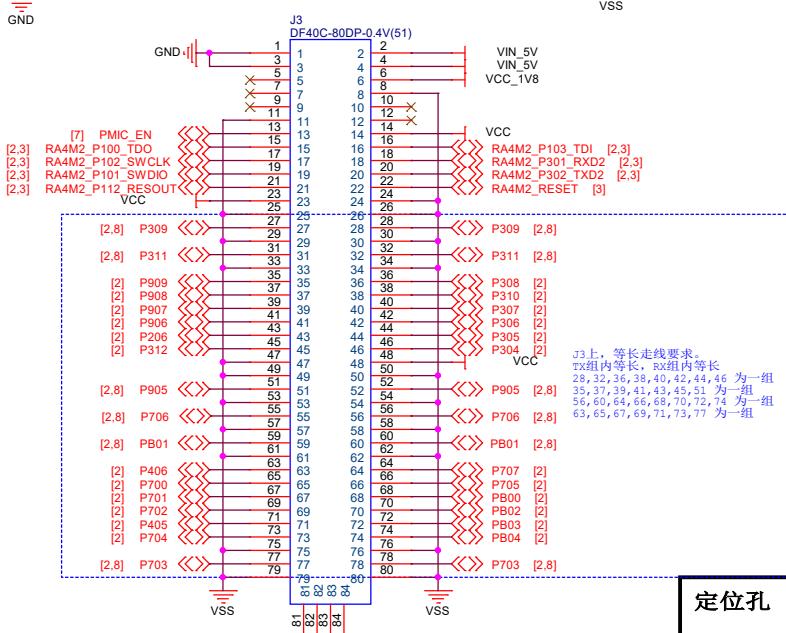
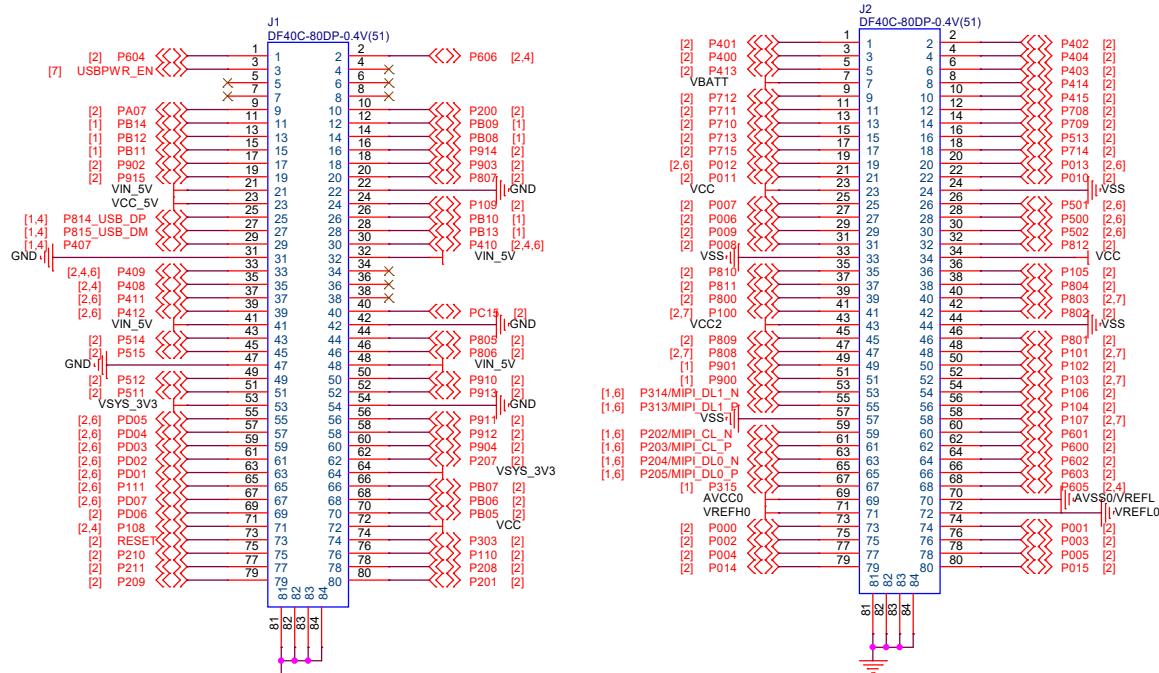
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BTB座子

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定位孔

SS801
NPTH_M2
SS802
NPTH_M2
SS803
NPTH_M2
SS804
NPTH_M2

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历史版本

版本号	日期	设计	描述
V1.0	2025-08-28	LPC	初始版本
V1.1	2025-09-17	LPC	修正VCC_USB连接

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